

Complementary N- and P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY

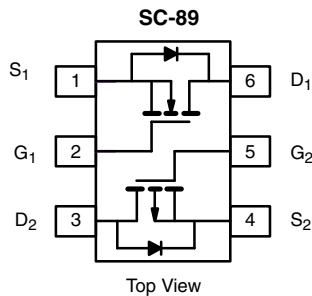
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (mA)
N-Channel	20	5 at $V_{GS} = 4.5$ V	200
		7 at $V_{GS} = 2.5$ V	175
		9 at $V_{GS} = 1.8$ V	150
		10 at $V_{GS} = 1.5$ V	50
P-Channel	- 20	8 at $V_{GS} = - 4.5$ V	- 150
		12 at $V_{GS} = - 2.5$ V	- 125
		15 at $V_{GS} = - 1.8$ V	- 100
		20 at $V_{GS} = - 1.5$ V	- 30

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET: 1.5 V Rated
- Very Small Footprint
- High-Side Switching
- Low On-Resistance:
N-Channel, 5 Ω
P-Channel, 8 Ω
- Low Threshold: ± 0.9 V (typ.)
- Fast Switching Speed: 45 ns (typ.)
- 1.5 V Operation
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE



Marking Code: M

Ordering Information: Si1035X-T1-GE3 (Lead (Pb)-free and Halogen-free)

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

APPLICATIONS

- Replace Digital Transistor, Level-Shifter
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter		Symbol	N-Channel		P-Channel		Unit
			5 s	Steady State	5 s	Steady State	
Drain-Source Voltage		V _{DS}	20		- 20		V
Gate-Source Voltage		V _{GS}	± 5				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	190	180	- 155	- 145	mA
	T _A = 85 °C		140	130	- 110	- 105	
Pulsed Drain Current ^b		I _{DM}	650		- 650		
Continuous Source Current (Diode Conduction)		I _S	450	380	- 450	- 380	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	280	250	280	250	mW
	T _A = 85 °C		145	130	145	130	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				°C
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000				V

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	0.40			V
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.40			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 2.8 V	N-Ch		± 0.5	± 1.0	μA
			P-Ch		± 0.5	± 1.0	
		V _{DS} = 0 V, V _{GS} = ± 4.5 V	N-Ch		± 1.5	± 3.0	
			P-Ch		± 1.0	± 3.0	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V	N-Ch		1	500	nA
		V _{DS} = - 16 V, V _{GS} = 0 V	P-Ch		- 1	- 500	
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 85 °C	N-Ch			10	μA
		V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C	P-Ch			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	N-Ch	250			mA
		V _{DS} = - 5 V, V _{GS} = - 4.5 V	P-Ch	- 200			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 200 mA	N-Ch			5	Ω
		V _{GS} = - 4.5 V, I _D = - 150 mA	P-Ch			8	
		V _{GS} = 2.5 V, I _D = 175 mA	N-Ch			7	
		V _{GS} = - 2.5 V, I _D = 125 mA	P-Ch			12	
		V _{GS} = 1.8 V, I _D = 150 mA	N-Ch			9	
		V _{GS} = - 1.8 V, I _D = - 100 mA	P-Ch			15	
		V _{DS} = 1.5 V, I _D = 40 mA	N-Ch			10	
		V _{DS} = - 1.5 V, I _D = - 30 mA	P-Ch			20	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 200 mA	N-Ch		0.5		S
		V _{DS} = - 10 V, I _D = - 150 mA	P-Ch		0.4		
Diode Forward Voltage ^a	V _{SD}	I _S = 150 mA, V _{GS} = 0 V	N-Ch			1.2	V
		I _S = - 150 mA, V _{GS} = 0 V	P-Ch			- 1.2	
Dynamic ^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 150 mA P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 150 mA	N-Ch		750		pC
Gate-Source Charge	Q _{gs}		P-Ch		1500		
			N-Ch		75		
			P-Ch		150		
Gate-Drain Charge	Q _{gd}	N-Ch		225			
		P-Ch		450			
Turn-On Time	t _{ON}	N-Channel V _{DD} = 10 V, R _L = 47 Ω I _D ≅ 250 mA, V _{GEN} = 4.5 V, R _g = 10 Ω	N-Ch			75	ns
			P-Ch			80	
Turn-Off Time	t _{OFF}	P-Channel V _{DD} = - 10 V, R _L = 65 Ω I _D ≅ - 150 mA, V _{GEN} = - 4.5 V, R _g = 10 Ω	N-Ch			75	
			P-Ch			90	

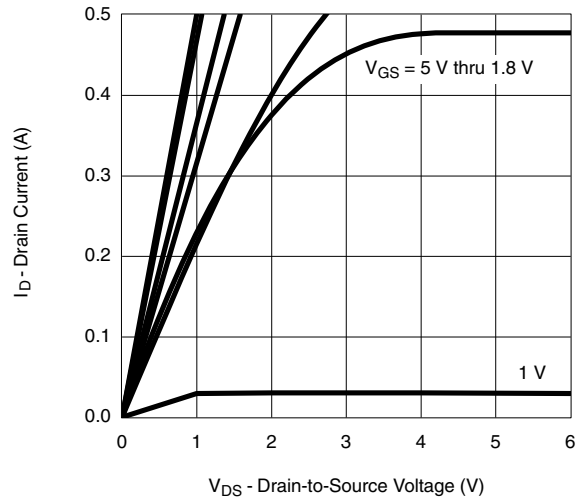
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

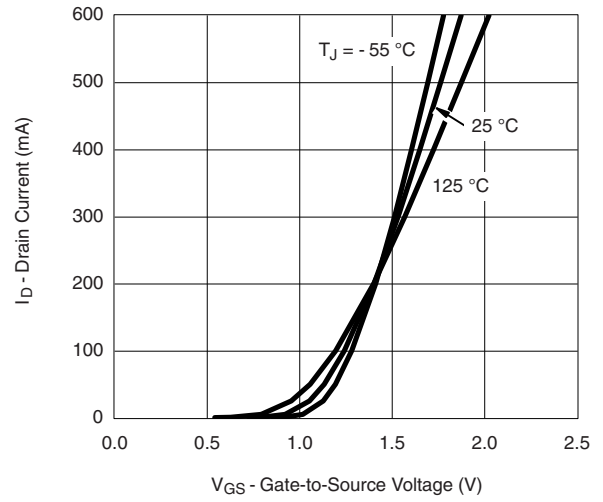
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

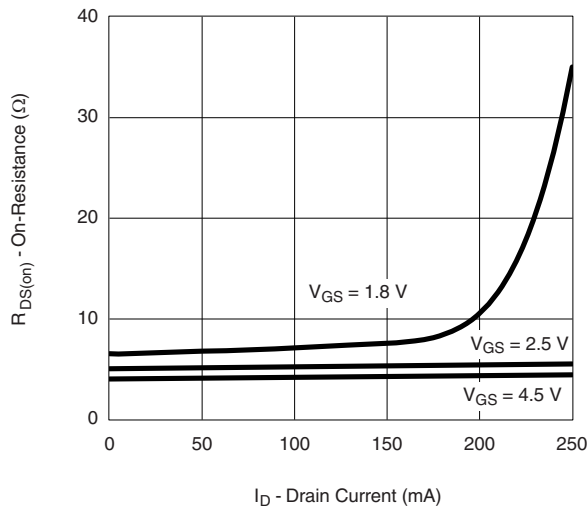
N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



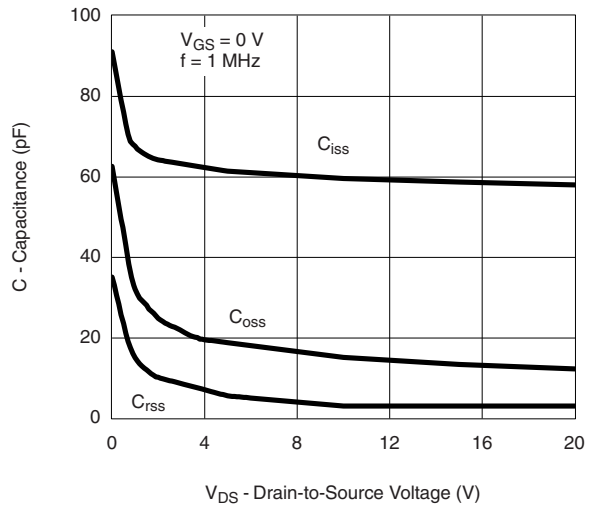
Output Characteristics



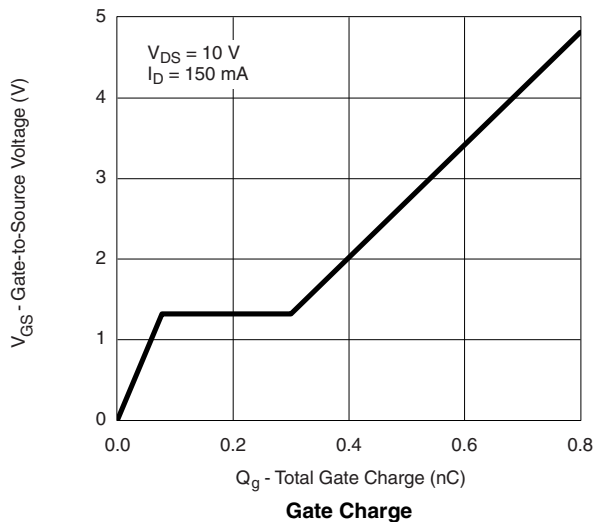
Transfer Characteristics



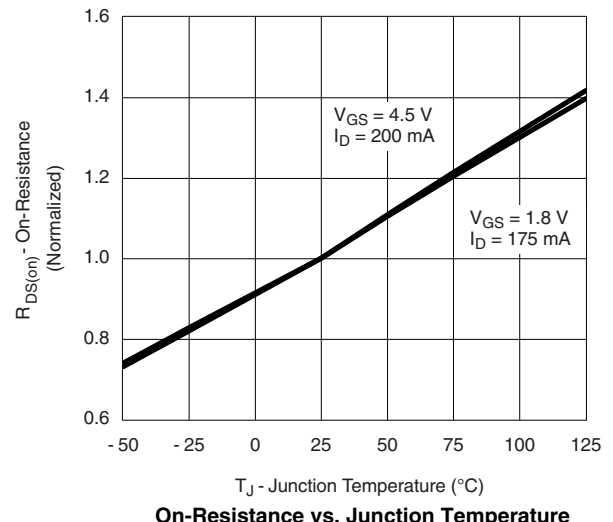
On-Resistance vs. Drain Current



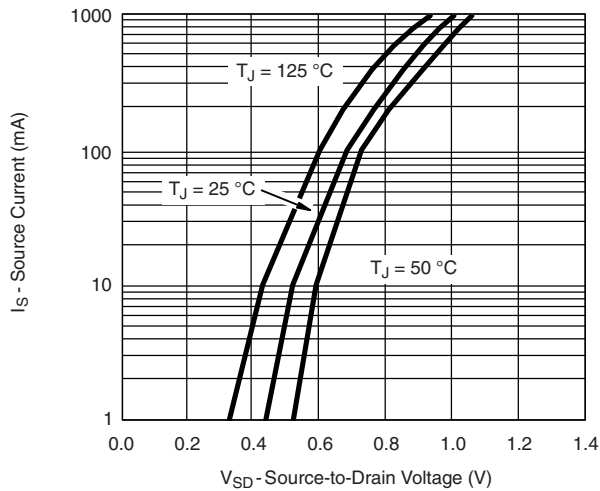
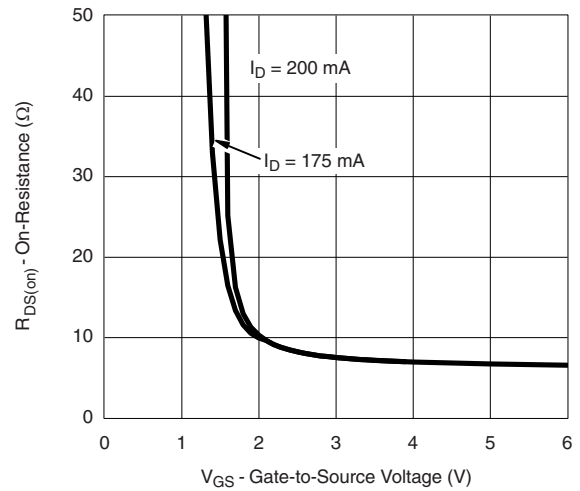
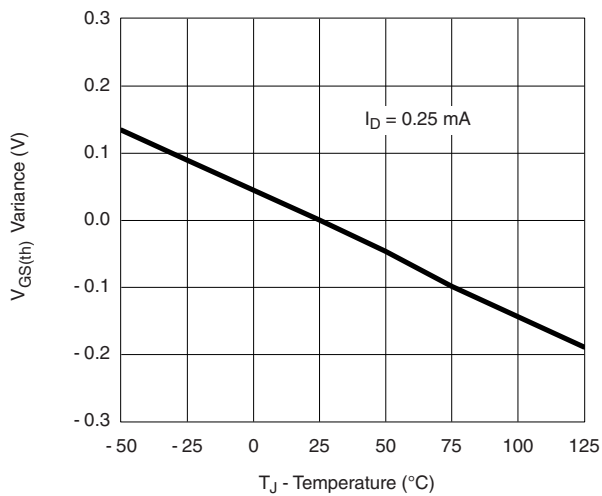
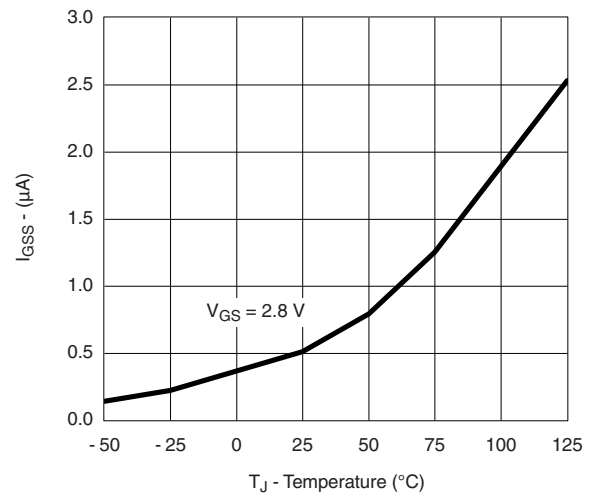
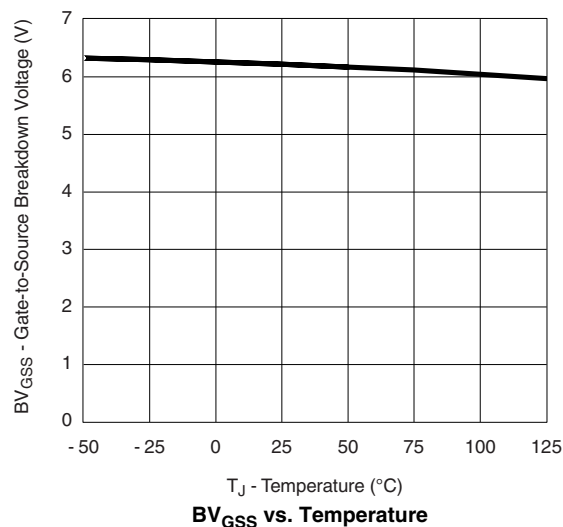
Capacitance



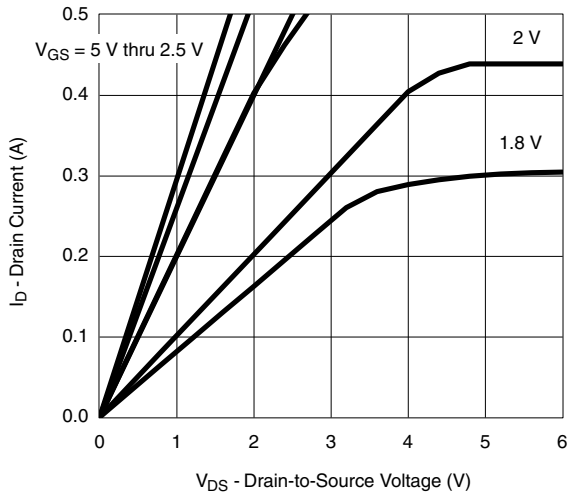
Gate Charge



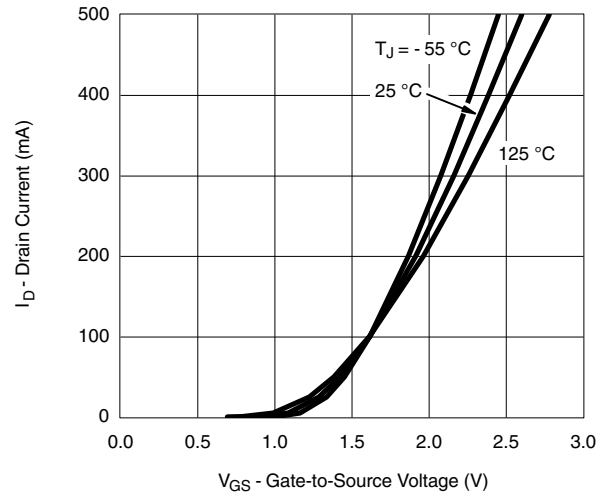
On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage Variance vs. Temperature

 I_{GSS} vs. Temperature

 BV_{GSS} vs. Temperature

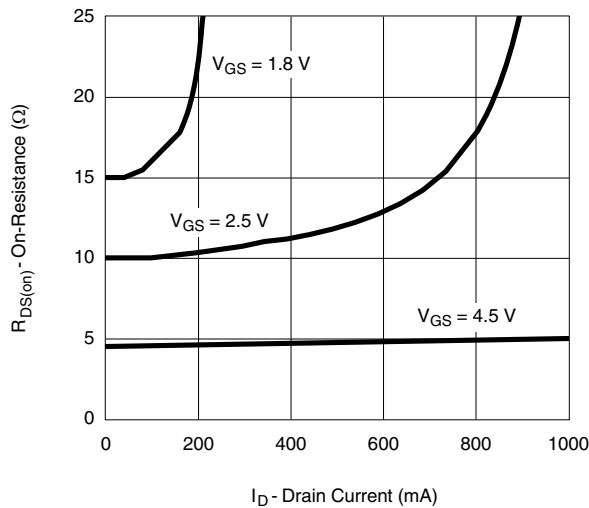
P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



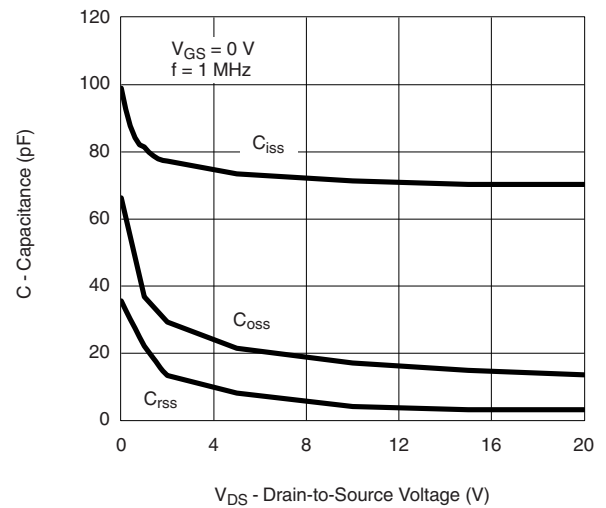
Output Characteristics



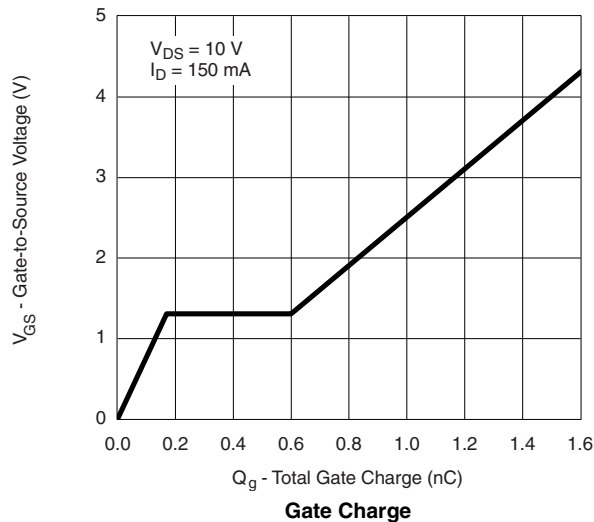
Transfer Characteristics



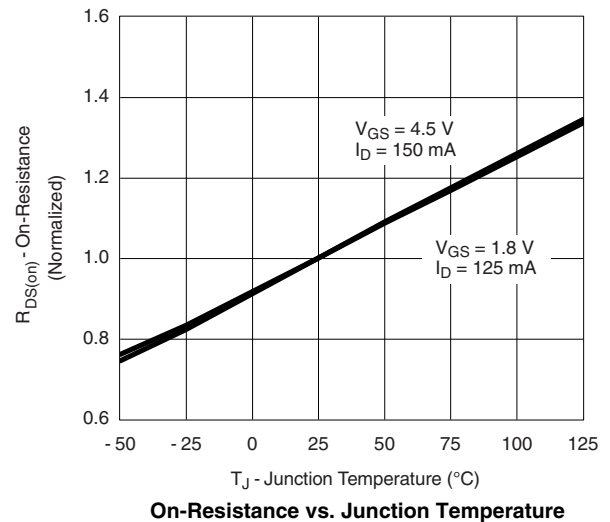
On-Resistance vs. Drain Current



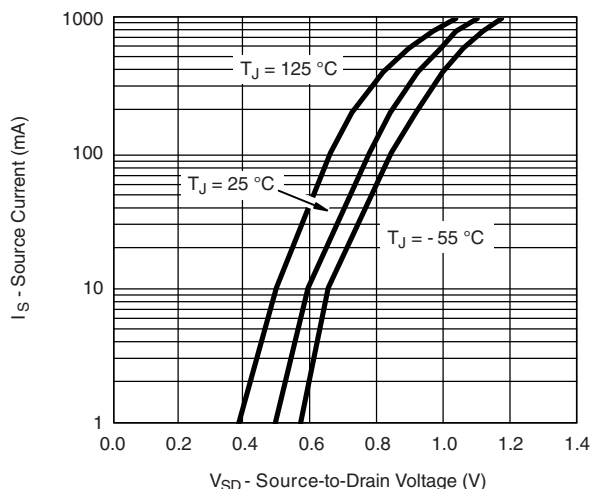
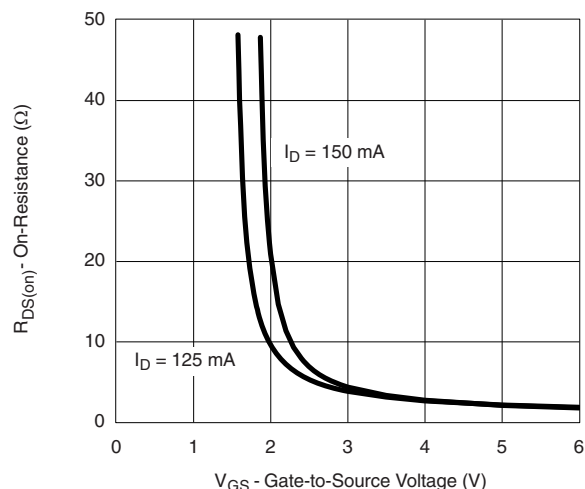
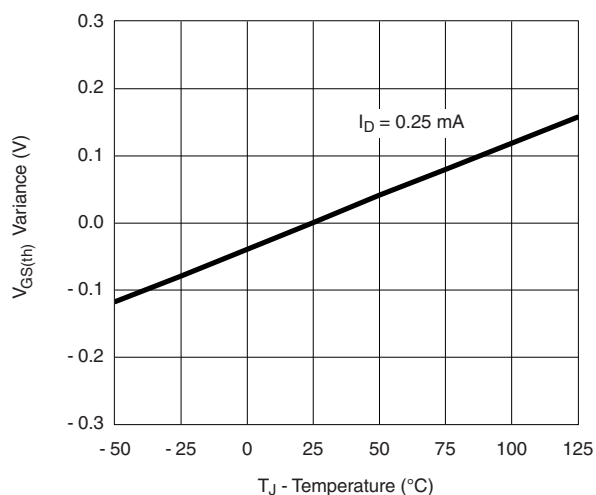
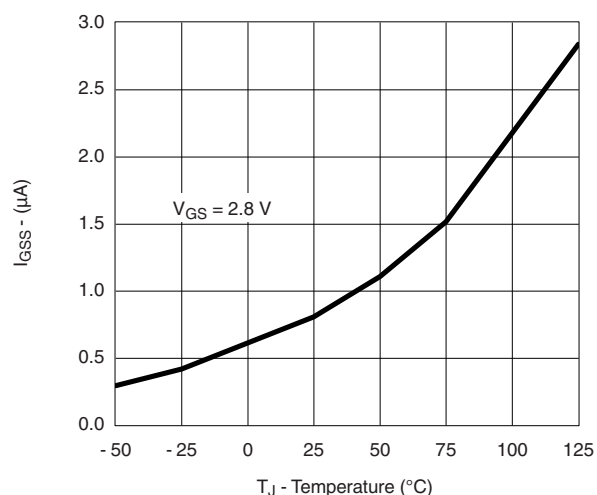
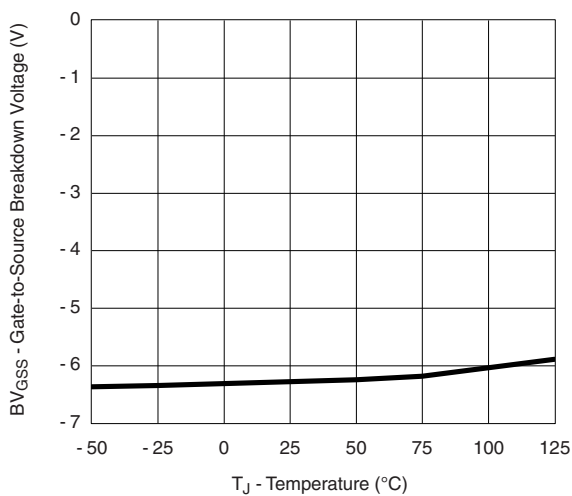
Capacitance

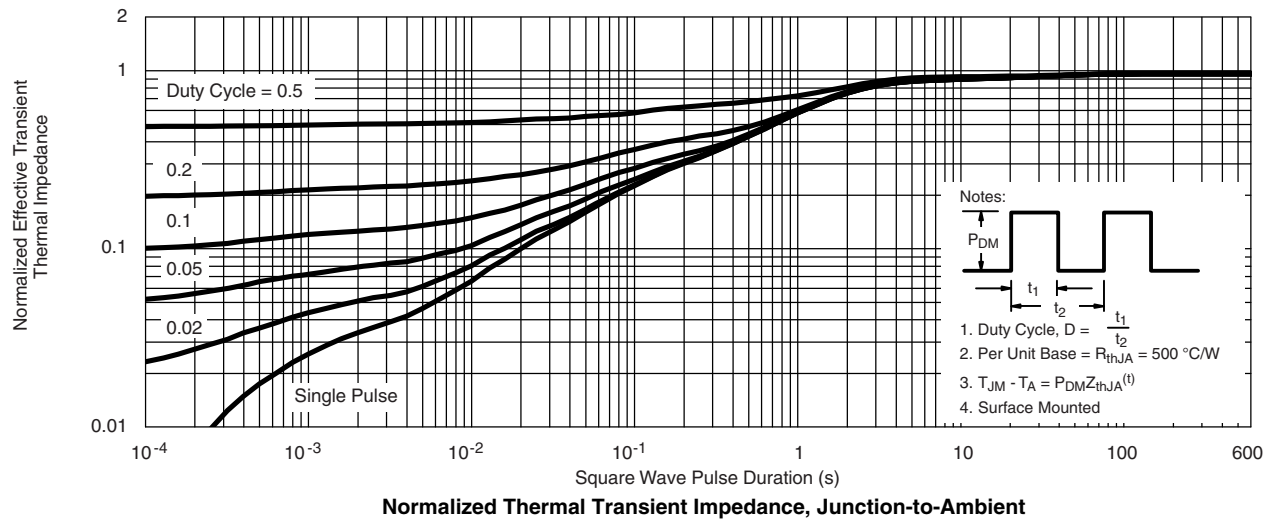


Gate Charge



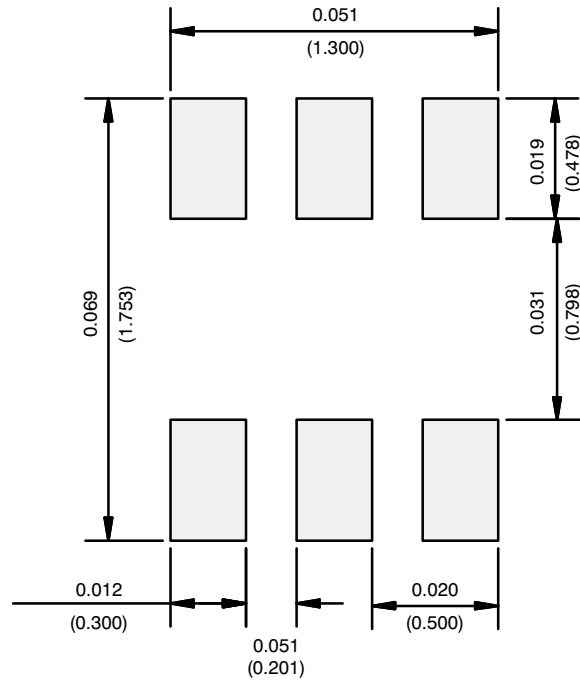
On-Resistance vs. Junction Temperature

P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage Variance vs. Temperature** **I_{GSS} vs. Temperature** **BV_{GSS} vs. Temperature**

N- OR P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71426.

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.